

providing a semiconductor wafer with a wafer surface having a plurality of circuit elements formed thereon;

forming on the wafer surface a plurality of electrodes connected to the circuit elements;

inserting the wafer into a burn-in apparatus;

testing the circuit elements in the burn-in apparatus for electrical functions, through the electrodes, with the wafer exposed to convective air in the burn-in apparatus; and

dividing the wafer into a plurality of semiconductor devices.

22. A method according to claim 21, wherein said dividing includes dividing the wafer after said testing.

23. A method according to claim 22, further comprising:
mounting the wafer on a circuit board with an elastic sheet interposed therebetween, including electrically connecting wiring circuits on the circuit board to the electrodes on the wafer through conductive elastic portions of the elastic sheet.

24. A method according to claim 23, further comprising:
disposing over the wafer a holding plate having a through hole; and
pressing the wafer on the circuit board with the holding plate.

25. A method according to claim 22, further comprising:
mounting the wafer on a circuit board with a film interposed therebetween,
including electrically connecting wiring circuits on the circuit board to the
electrodes on the wafer through bump electrodes in the film.

26. A method according to claim 25, further comprising:
disposing over the wafer a holding plate having a through hole; and
pressing the wafer on the circuit board with the holding plate.

27. A method according to claim 21, further comprising the step of
forming a plurality of solder balls as the electrodes.

-- 42. (New) A method according to claim 24, further comprising providing
the convective air over the wafer through the through hole.

43. (New) A method according to claim 26, further comprising providing the
convective air over the wafer through the through hole.

44. (New) A method for manufacturing semiconductor devices, the method
comprising:

preparing a semiconductor wafer with a first and surface and a second
surface, the second surface being opposite to the first surface, wherein the first
surface has a plurality of circuit elements formed thereon;

forming a plurality of electrodes on the first surface, the electrodes being connected to the circuit elements;

inserting the semiconductor wafer into a burn-in apparatus;

testing the circuit elements in the burn-in apparatus for electrical function, through the electrodes, with the second surface of the semiconductor wafer exposed to convective air in the burn-in apparatus; and

dividing the semiconductor wafer into the plurality of semiconductor devices.

45. (New) A method according to claim 44, wherein the dividing includes dividing the semiconductor wafer after the testing.

46. (New) A method according to claim 45, further comprising mounting the semiconductor wafer on a circuit board with an elastic sheet interposed therebetween, including electrically connecting wiring circuits on the circuit board to the electrodes on the semiconductor wafer through conductive elastic portions of the elastic sheet.

47. (New) A method according to claim 46, further comprising:

disposing over the semiconductor wafer a holding plate having a through hole; and

pressing the semiconductor wafer on the circuit board with the holding plate.

48. (New) A method according to claim 45, further comprising mounting the semiconductor wafer on a circuit board with a film interposed therebetween, including electrically connecting wiring circuits on the circuit board to the electrodes on the semiconductor wafer through bump electrodes in the film.

49. (New) A method according to claim 48, further comprising:
disposing over the semiconductor wafer a holding plate having a through hole, and
pressing the semiconductor wafer on the circuit board with the holding plate.

50. (New) A method according to claim 44, further comprising forming a plurality of solder balls as the electrodes.

51. (New) A method according to claim 47, further comprising providing the convective air over the second surface of the semiconductor wafer through the through hole.

52. (New) A method according to claim 49, further comprising providing the convective air over the second surface of the semiconductor wafer through the through hole. --